

## ABSTRACT

The present invention relates to a method of forming a well in a semiconductor device. After a sidewall oxidization process of a trench formed by a shallow trench isolation technology is performed, an additional ion implantation process is performed. In the above, the additional ion implantation process includes implanting an impurity onto the sidewalls of the trench using a deflected ion beam and implanting the ion by rotating the device 4 times. Therefore, the impurity can be implanted into all the sidewalls of the trench. It is possible to improve characteristics of the device due to formation of a well in which the doping concentration of the impurity ion is uniform.